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Kind regards,

Team Nexperia



BC856S 65 V, 100 mA PNP/PNP general-purpose transistor Rev. 02 – 19 February 2009 Produ

Product data sheet

1. Product profile

1.1 General description

PNP/PNP general-purpose transistor pair in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

1.2 Features

- Low collector capacitance
- Low collector-emitter saturation voltage
- Closely matched current gain
- Reduces number of components and board space
- No mutual interference between the transistors

1.3 Applications

General-purpose switching and amplification

1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
V_{CEO}	collector-emitter voltage	open base	-	-	-65	V
I _C	collector current		-	-	-100	mA
h _{FE}	DC current gain	V _{CE} = -5 V; I _C = -2 mA	110	-	-	

2. Pinning information

Pin	Description	Simplified outline	Graphic symbol
1	emitter TR1		
2	base TR1		
3	collector TR2		
4	emitter TR2		
5	base TR2		
6	collector TR1		1 2 3
			sym018



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3. Ordering information

Table 3. Order	ing inform	ation	
Type number	Package		
	Name	Description	Version
BC856S	SC-88	plastic surface-mounted package; 6 leads	SOT363

4. Marking

Table 4.Marking codes

Type number	Marking code ^[1]
BC856S	5F*

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

5. Limiting values

Table 5. Limiting values

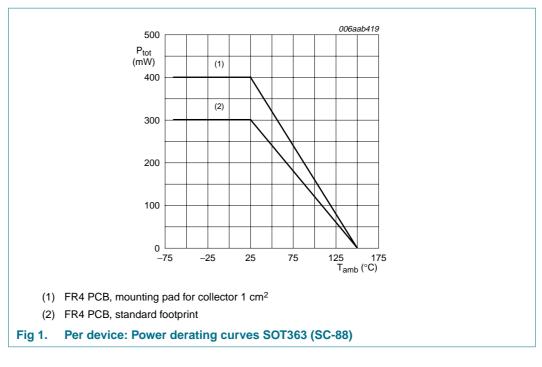
In accordance with the Absolute Maximum Rating System (IEC 60134).

			-		
Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V _{CBO}	collector-base voltage	open emitter	-	-80	V
V _{CEO}	collector-emitter voltage	open base	-	-65	V
V _{EBO}	emitter-base voltage	open collector	-	-5	V
I _C	collector current		-	-100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> _	220	mW
			[2] _	250	mW
Per device					
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> _	300	mW
			[2] _	400	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

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6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> _	-	568	K/W
			[2] _	-	500	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	230	K/W
Per device	;					
R _{th(j-a)}	thermal resistance from	in free air	<u>[1]</u> -	-	416	K/W
	junction to ambient		[2] _	-	313	K/W

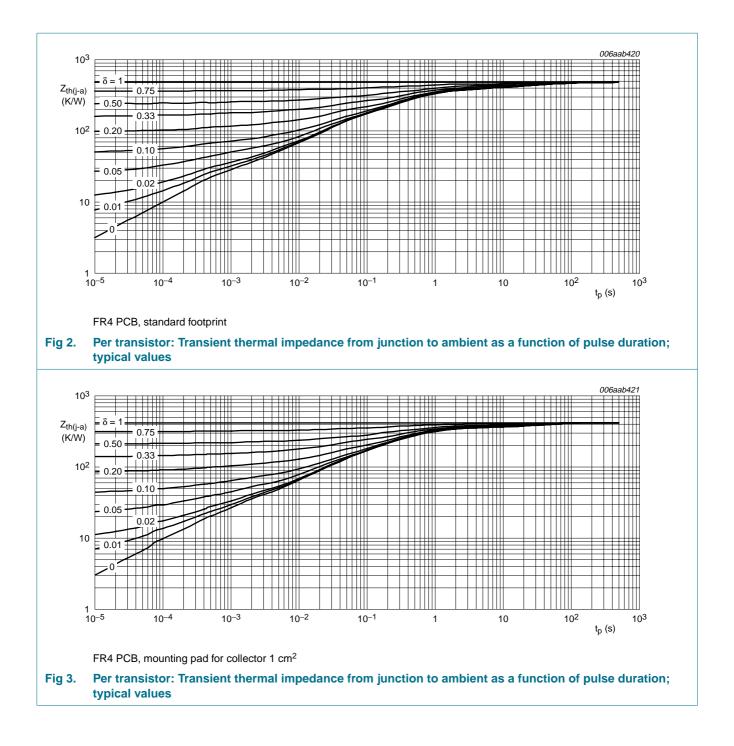
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

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65 V, 100 mA PNP/PNP general-purpose transistor

BC856S



65 V, 100 mA PNP/PNP general-purpose transistor

7. Characteristics

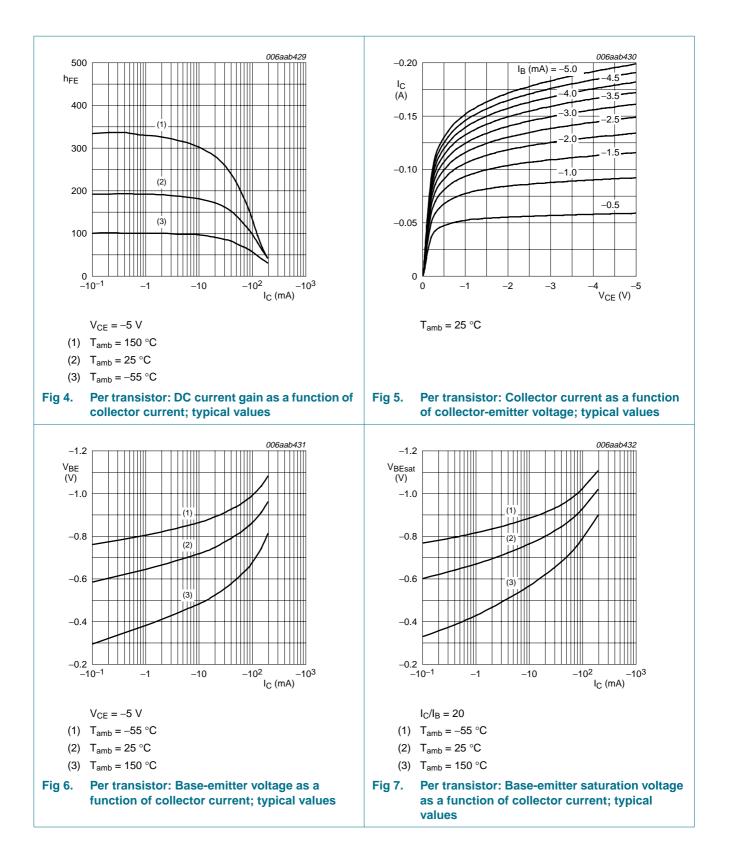
Table 7.Characteristics $T_{amb} = 25 ^{\circ}C$ unless otherwise specified.							
Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Per trans	Per transistor						
I _{CBO} collector-base current	collector-base cut-off	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}$	-	-	-15	nA	
	current	$V_{CB} = -30 \text{ V}; \text{ I}_{E} = 0 \text{ A};$ T _j = 150 °C	-	-	-5	μΑ	
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	-100	nA	
h _{FE}	DC current gain	V_{CE} = -5 V; I_C = -2 mA	110	-	-		
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = -10 \text{ mA};$ $I_{B} = -0.5 \text{ mA}$	-	-	-100	mV	
		$I_{\rm C} = -100 \text{ mA}; I_{\rm B} = -5 \text{ mA}$	1 -	-	-300	mV	
V _{BEsat}	base-emitter saturation voltage	I _C = -10 mA; I _B = -0.5 mA	-	700	-	mV	
V_{BE}	base-emitter voltage	$I_C = -2 \text{ mA}; V_{CE} = -5 \text{ V}$	-600	-650	-750	mV	
		$I_{C} = -10 \text{ mA}; V_{CE} = -5 \text{ V}$	-	-	-820	mV	
C _c	collector capacitance	$I_E = i_e = 0 \text{ A}; V_{CB} = -10 \text{ V};$ f = 1 MHz	-	-	2.5	pF	
f _T	transition frequency	$I_{C} = -10 \text{ mA}; V_{CE} = -5 \text{ V};$ f = 100 MHz	100	-	-	MHz	

[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02$.

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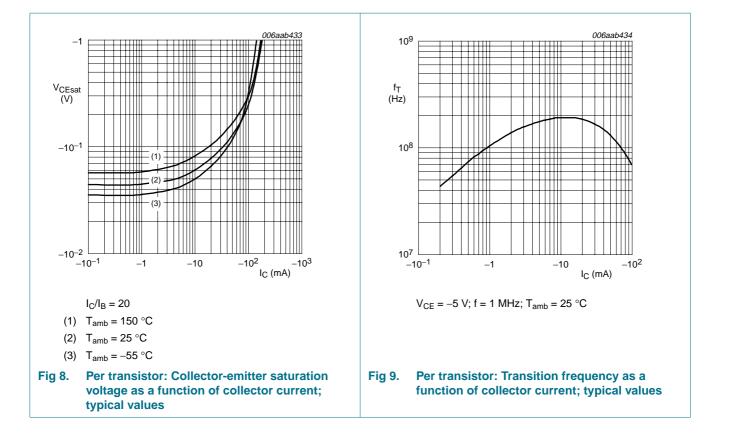


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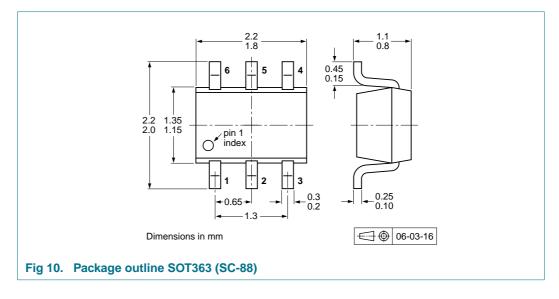
BC856S

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65 V, 100 mA PNP/PNP general-purpose transistor

8. Package outline



9. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Package Description		Packing	g quantity
				3000	10000
BC856S SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-135	
		4 mm pitch, 8 mm tape and reel; T2	<u>[3]</u>	-125	-165

[1] For further information and the availability of packing methods, see <u>Section 13</u>.

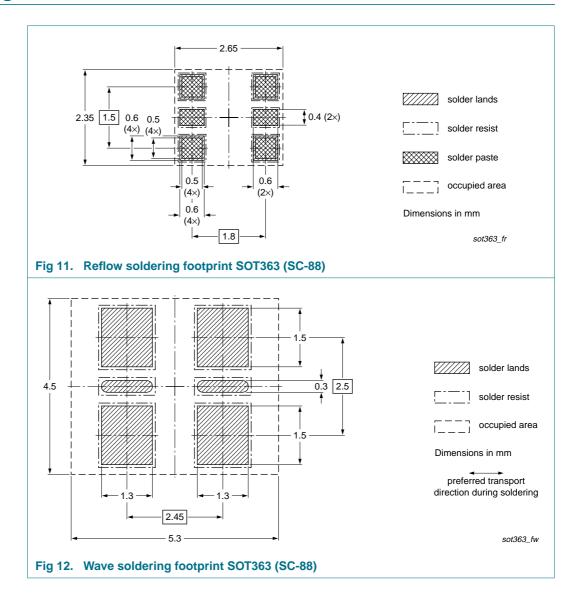
[2] T1: normal taping

[3] T2: reverse taping

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10. Soldering



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11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BC856S_2	20090219	Product data sheet	-	BC856S_1		
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 					
	 Legal texts have been adapted to the new company name where appropriate. 					
	 <u>Section 1.2 "Features"</u>: adapted 					
	 Section 4 "Marking": updated 					
	 Section 7 "Characteristics": enhanced 					
	 Section 9 "Packing information": added 					
	Section 10 "Soldering": added					
	Section 12 "	_egal information": updated				
BC856S 1	19990824	Product specification	-	-		

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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